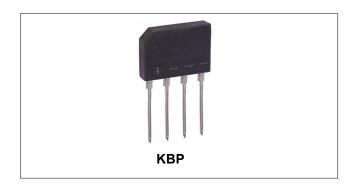






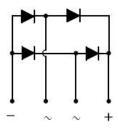
KBP2005G THRU KBP210G SINGLE PHASE 2.0AMP GLASS PASSIVATED BRIDGE RECTIFIER



Features

- Glass passivated die construction
- Low forward voltage drop
- · High current capability
- High surge current capability
- Plastic material-UL flammability 94V-0
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: KBP, molded plastic
- Terminals: plated leads solderable per MIL-STD-202, Method 208
- Polarity: as marked on case
- Mounting position: Any
- Lead Free: For RoHS / Lead Free Version

Maximum Ratings: @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Type number	Symbol	KBP 2005G	KBP 201G	KBP 202G	KBP 204G	KBP 206G	KBP 208G	KBP 210G	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Average Rectified Output Current @ T _A =50°C	Io	2.0						А	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	60					А		

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Electrical Characteristics:

Type Number	Symbol	KBP 2005G	KBP 201G	KBP 202G	KBP 204G	KBP 206G	KBP 208G	KBP 210G	Units
Forward Voltage per element @I _F =2.0A	VF	1.1						v	
Peak Reverse Current @T _A =25°C At Rated DC Blocking Voltage @T _A =125°C	I _R	5.0 500						μА	

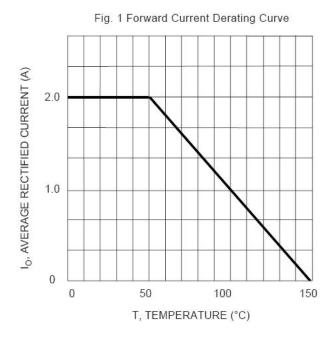
^{*} Pulse width < 300 μ s, duty cycle < 2%

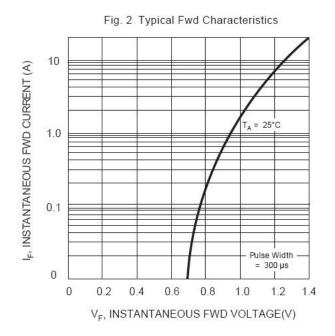
Thermal-Mechanical Specifications:

Type Number	Symbol	KBP 2005G	KBP 201G	KBP 202G	KBP 204G	KBP 206G	KBP 208G	KBP 210G	Units
Typical Thermal Resistance Junction to Ambient (Note 1)	$R_{\theta JA}$	R _{0JA} 25						°C/W	
Typical Thermal Resistance Junction to Lead (Note 1)	$R_{\theta JL}$	R _{eJL} 8					C/VV		
Junction Temperature	T _J -55 to +150					°C			
Storage Temperature Range	T _{STG}	-55 to +150					°C		
Approximate Weight	wt	wt 1.4					g		
Case Style	KBP								

Note: 1. Mounted on glass epoxy PC board with 1.3mm² solder pad.

Ratings and Characteristics Curves





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Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

100
Single Half Sine-Wave Pulse Width = 8.3ms (JEDEC Method)

40
0
10
10
NUMBER OF CYCLES AT 60 Hz

Fig. 4 Typical Junction Capacitance

100

T_J=25°C

f=1MHz

10

10

10

10

10

10

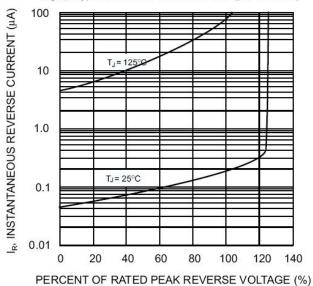
10

10

10

V_R, REVERSE VOLTAGE (V)

Fig. 5 T ypical Reverse Characteristics (per element)



Ordering Information

Device	Package	Shipping			
KBP2005G THRU KBP210G	KBP(Pb-Free)	35pcs / tube			

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

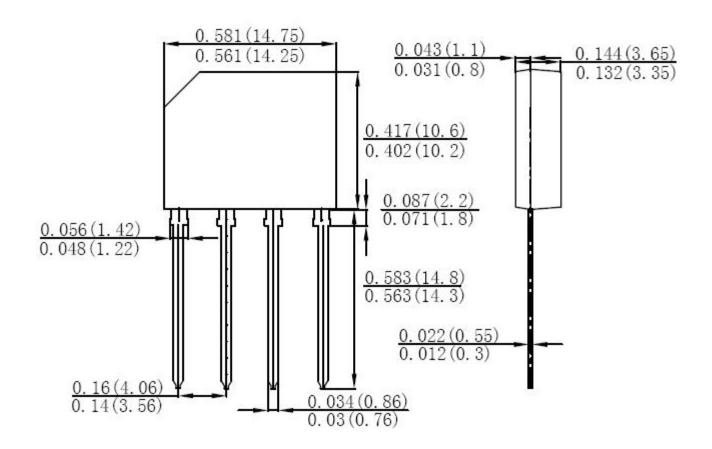
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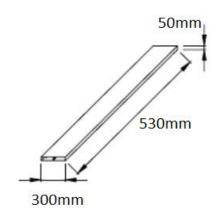




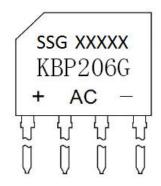
Mechanical Dimensions KBP (Inches/Millimeters)



Tube Specification



Marking Diagram



Where XXXXX is YYWWL

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

 KBP206G
 = Type Number

Cautions: Molding resin Epoxy resin UL:94V-0

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